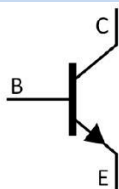


Silicon NPN transistor in a TO-220 Plastic Package.

High voltage switching transistor.

Switching regulator and general purpose.



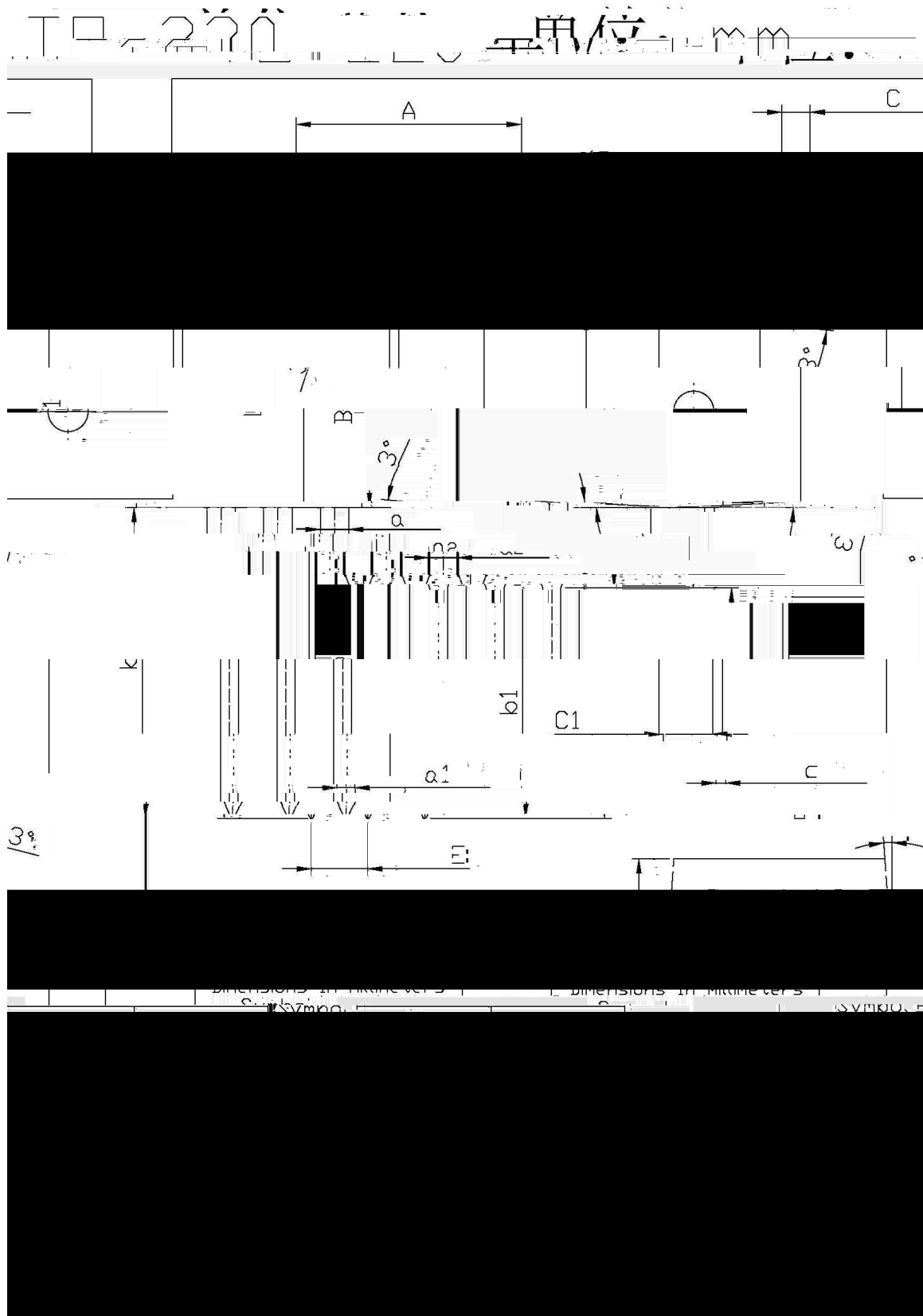
PIN1 Base PIN 2 Collector PIN 3 Emitter

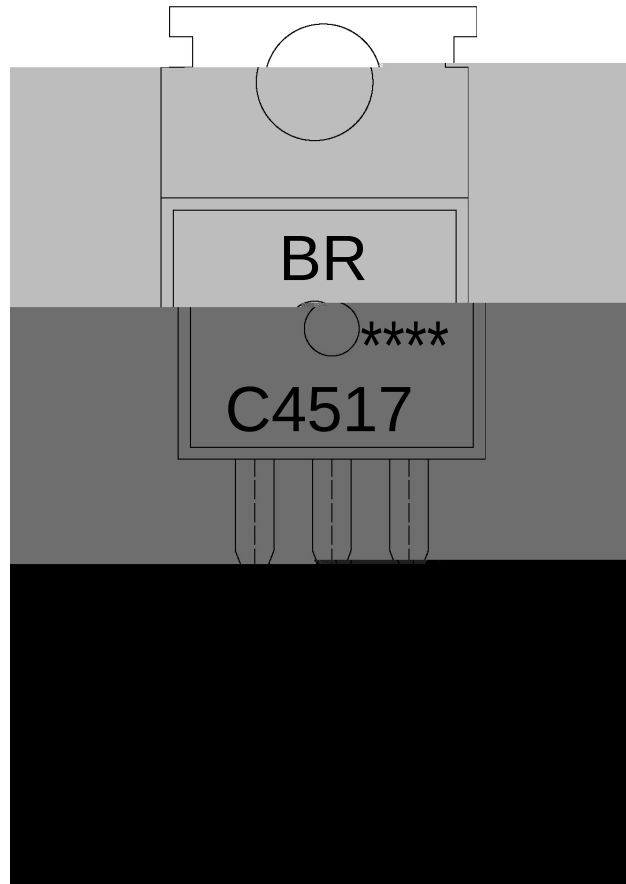
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	900	V
Collector to Emitter Voltage	V_{CEO}	550	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current - Continuous	I_B	1.5	A
Collector Power Dissipation	P_C	30	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

T

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=800V$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=7.0V$ $I_C=0$			100	μA
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA$ $I_B=0$	550			V
DC Current Gain	h_{FE}	$V_{CE}=4.0V$ $I_C=1.0A$	10		30	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0A$ $I_B=0.2A$			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1.0A$ $I_B=0.2A$			1.2	V
Transition Frequency	f_T	$V_{CE}=12V$ $I_E=-0.25A$		6		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$		35		pF





Note:

BR: Company Code

C4517: Product Type.

****: Lot No. Code, code change with Lot No.

